8-Bit Shift and Store Register

High-Performance Silicon-Gate CMOS

The MC74HC4094A is a high speed CMOS 8—bit serial shift and storage register. This device consists of an 8—bit shift register and latch with 3—state output buffers. Data is shifted on positive clock (CP) transitions. The data in the shift register is transferred to the storage register when the Strobe (STR) input is high. The output buffers are enabled when the Output Enable (OE) input is set high. Two serial outputs (QS1, QS2) are available for cascading multiple devices.

Features

- Wide Operating Voltage Range: 2.0 to 6.0 V
- Low Power Dissipation: $I_{CC} = < 10 \mu A$
- In Compliance with the Requirements Defined by JEDEC Standard No. 7A
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These are Pb-Free Devices

Typical Applications

- Serial-to-Parallel Conversion
- Remote Control Storage Register



ON Semiconductor®

www.onsemi.com

MARKING DIAGRAMS

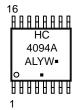


SOIC-16 D SUFFIX CASE 751B





TSSOP-16 DT SUFFIX CASE 948F



A = Assembly Location

WL, L = Wafer Lot YY, Y = Year WW, W = Work Week G, • = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 10 of this data sheet.

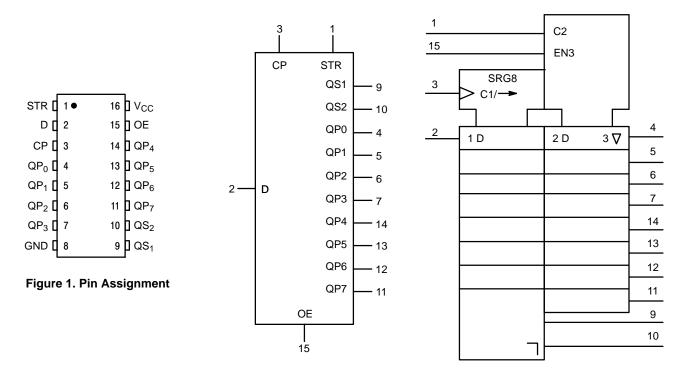


Figure 2. Logic Symbol

Figure 3. IEC Logic Symbol

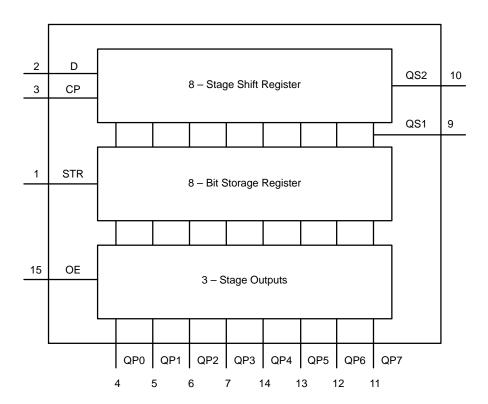


Figure 4. Functional Diagram

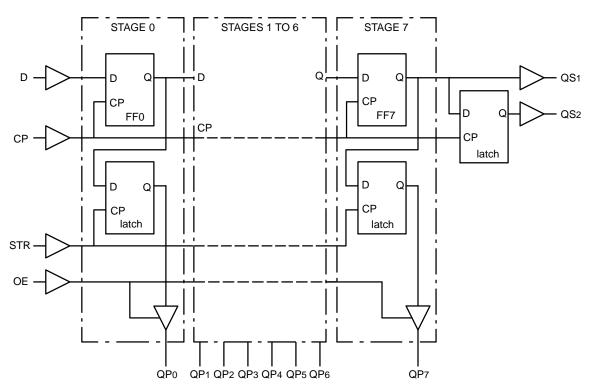


Figure 5. Logic Diagram

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	DC Supply Voltage (Referenced to GND)	- 0.5 to + 7.0	V
V _{in}	DC Input Voltage (Referenced to GND)	-0.5 to $V_{CC} + 0.5$	V
V _{out}	DC Output Voltage (Referenced to GND)	-0.5 to $V_{CC} + 0.5$	V
I _{in}	DC Input Current, per Pin	± 20	mA
I _{out}	DC Output Current, per Pin	± 35	mA
I _{CC}	DC Supply Current, V _{CC} and GND Pins	± 75	mA
P _D	Power Dissipation in Still Air, SOIC Package† TSSOP Package†	500 450	mW
T _{stg}	Storage Temperature	- 65 to + 150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

†Derating – SOIC Package: – 7 mW/°C from 65° to 125°C TSSOP Package: – 6.1 mW/°C from 65° to 125°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND \leq (V_{in} or V_{out}) \leq V_{CC} .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or $V_{\rm CC}$). Unused outputs must be left open.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit	
V _{CC}	DC Supply Voltage (Referenced to G	2.0	6.0	V	
V _{in} , V _{out}	DC Input Voltage, Output Voltage (Referenced to GND)	0	V _{CC}	V	
T _A	Operating Temperature, All Package	Types	- 55	+125	°C
t _r , t _f	Input Rise and Fall Time (Figure 1)	V _{CC} = 2.0 V V _{CC} = 4.5 V V _{CC} = 6.0 V	0 0 0	1000 500 400	ns

FUNCTIONAL TABLE

	INPUTS			PARALLEL OUTPUTS		SERIAL OUTPUTS	
СР	OE	STR	D	QP0	QPn	QS1	QS2
1	L	Х	Х	Z	Z	Q'6	NC
\downarrow	L	Х	Х	Z	Z	NC	QP7
1	Н	L	Х	NC	NC	Q'6	NC
1	Н	Н	L	L	QPn-1	Q'6	NC
1	Н	Н	Н	Н	QPn-1	Q'6	NC
\downarrow	Н	Н	Н	NC	NC	NC	QP7

Notes

- 1. H = HIGH voltage level
 - L = LOW voltage level
 - X = don't care
 - Z = high impedance OFF-state

 - NC = no change

 ↑ = LOW-to-HIGH CP transition

 ↓ = HIGH-to-LOW CP transition

 - Q'6 = the information in the seventh register stage is transferred to the 8th register stage and QSn output at the positive clock edge

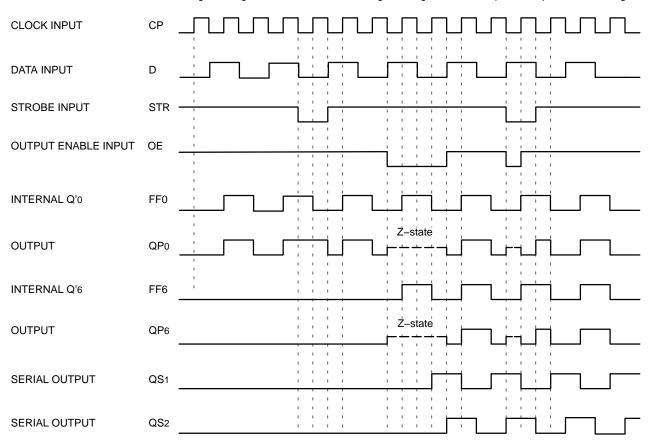


Figure 6. Timing Diagram

DC CHARACTERISTICS

				Guaranteed Limits			
Symbol	Parameter	Test Conditions	V _{CC} (V)	-55°C to 25°C	≤ 85°C	≤ 125°C	Uni
V_{IH}	V _{IH} Minimum High–Level Input Voltage	High-Level Input $V_{OUT} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$		1.5	1.5	1.5	V
		I _{OUT} ≤ 20 μA	3.0	2.1	2.1	2.1	
			4.5	3.15	3.15	3.15	
			6.0	4.2	4.2	4.2	
V_{IL}	Maximum Low-Level Input	$V_{OUT} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$	2.0	0.5	0.5	0.5	V
	Voltage	I _{OUT} ≤ 20 μA	3.0	0.9	0.9	0.9	
			4.5	1.35	1.35	1.35	
			6.0	1.8	1.8	1.8	
V _{OH}	Minimum High-Level Output	V _{IN} = V _{IH} or V _{IL}	2.0	1.9	1.9	1.9	V
	Voltage	lout l≤ 20 μA	3.0	2.9	2.9	2.9	
			4.5	4.4	4.4	4.4	
			6.0	5.9	5.9	5.9	
		$V_{IN} = V_{IH}$ or V_{IL} , $ _{OUT} = 2.4$ mA	3.0	2.75	2.7	2.6	
		V _{IN} = V _{IH} or V _{IL} , I _{OUT} = 4 mA	4.5	4.25	4.2	4.1	
		$V_{IN} = V_{IH}$ or V_{IL} , $ _{OUT} = 5.2$ mA	6.0	5.75	5.7	5.6	
V _{OL}	Maximum Low-Level Output	$V_{IN} = V_{IH} \text{ or } V_{IL}, _{OUT} \le 20 \mu A$	2.0	0.1	0.1	0.1	V
	Voltage		3.0	0.1	0.1	0.1	
			4.5	0.1	0.1	0.1	
			6.0	0.1	0.1	0.1	
		$V_{IN} = V_{IH}$ or V_{IL} , $ _{OUT} = 2.4$ mA	3.0	0.25	0.3	0.4	
		V _{IN} = V _{IH} or V _{IL} , I _{OUT} = 4 mA	4.5	0.25	0.3	0.4	
		$V_{IN} = V_{IH}$ or V_{IL} , $ _{OUT} = 5.2$ mA	6.0	0.25	0.3	0.4	
I _{IN}	Maximum Input Leakage Current	$V_{IN} = V_{CC}$ or GND	6.0	±0.1	±1	±1	μΑ
I _{OZ}	Maximum Tri-State Output Leakage Current	V _{IN} = V _{CC} or GND V _{OUT} = V _{CC} or GND	6.0	±0.5	±5	±10	μΑ
I _{CC}	Maximum Quiescent Supply Current	$V_{IN} = V_{CC}$ or GND	6.0	4.0	40	80	μA

AC CHARACTERISTICS ($t_f = t_r = 6 \text{ ns}, C_L = 50 \text{ pF}$)

				Guaranteed Limits			
Symbol	Parameter	Test Conditions	V _{CC} (V)	-55°C to 25°C	≤ 85°C	≤ 125°C	Unit
t _{PHL} , t _{PLH}	Maximum Propagation Delay	Figure 7	2.0	120	150	170	ns
	CP to QS ₁		3.0	90	100	110	
			4.5	30	38	45	
			6.0	26	33	38	
t _{PHL} , t _{PLH}	Maximum Propagation Delay	Figure 7	2.0	120	150	170	ns
	CP to QS ₂		3.0	90	100	110	
			4.5	27	34	41	
			6.0	23	29	35	
t _{PHL} , t _{PLH}	Maximum Propagation Delay	Figure 7	2.0	120	150	170	ns
	CP to QP _n		3.0	90	100	110	
			4.5	39	49	59	
			6.0	33	42	50	
t _{PHL} , t _{PLH}	Maximum Propagation Delay	Figure 8	2.0	120	150	170	ns
	STR to QP _n		3.0	90	100	110	
			4.5	36	45	54	
			6.0	31	38	46	
t _{PZH} , t _{PZL}	Maximum 3-State Output Enable Time	Figure 9	2.0	120	140	160	ns
	OE to QP _n		3.0	80	100	120	
			4.5	35	44	53	
			6.0	30	37	45	
t _{PHZ} , t _{PLZ}	Maximum 3-State Output Enable Time	Figure 9	2.0	100	120	140	ns
	OE to QP _n		3.0	70	90	110	
			4.5	25	31	38	
			6.0	21	26	32	
t _{THL} , t _{TLH}	Maximum Output Transition Time	Figure 7	2.0	70	90	110	ns
			3.0	40	60	80	
			4.5	18	22	25	
			6.0	16	19	22	
t _W	Minimum Clock Pulse Width	Figure 7	2.0	80	100	120	ns
	High or Low		3.0	50	60	80	
			4.5	16	20	24	
			6.0	14	17	20	
t _W	Minimum Strobe Pulse Width	Figure 8	2.0	80	100	120	ns
	High		3.0	50	60	80	
			4.5	16	20	24	
			6.0	14	17	20	
t _{SU}	Minimum Set-up Time	Figure 10	2.0	50	65	75	ns
	D to CP		3.0	30	35	45	
			4.5	10	13	15	
			6.0	9	11	13	1

AC CHARACTERISTICS ($t_f = t_r = 6 \text{ ns}, C_L = 50 \text{ pF}$)

				Guaranteed Limits			
Symbol	Parameter	Test Conditions	V _{CC} (V)	-55°C to 25°C	≤ 85°C	≤ 125°C	Unit
t _{SU}	Minimum Set-up Time	Figure 8	2.0	100	125	150	ns
	CP to STR		3.0	60	75	90	1
			4.5	20	25	30	1
			6.0	17	21	26	1
t _h	Minimum Hold Time	Figure 10	2.0	3	3	3	ns
	D to CP		3.0	3	3	3	1
			4.5	3	3	3	1
			6.0	3	3	3	1
t _h	Minimum Hold Time	Figure 8	2.0	0	0	0	ns
	CP to STR		3.0	0	0	0	1
			4.5	0	0	0	1
			6.0	0	0	0	
f _{MAX}	Minimum Clock Pulse Frequency	Figure 7	2.0	6	5	4	MHz
			3.0	18	14	12	
			4.5	30	24	20	
			6.0	35	28	24	
C _{in}	Maximum Input Capacitance		-	10	10	10	pF
C _{out}	Maximum Output Capacitance		-	15	15	15	pF
C _{PD}	Power Dissipation Capacitance (Note 2)		_	140	140	140	pF

^{2.} C_{PD} is defined as the value of the IC's equivalent capacitance from which the operating current can be calculated from: I_{CC} (operating) $\approx C_{PD} \times V_{CC} \times f_{IN} \times N_{SW}$ where N_{SW} = total number of outputs switching and f_{IN} = switching frequency.

AC WAVEFORMS

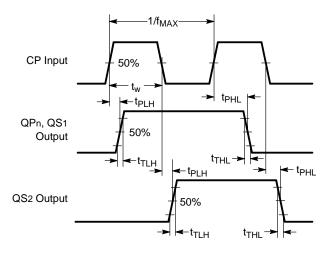
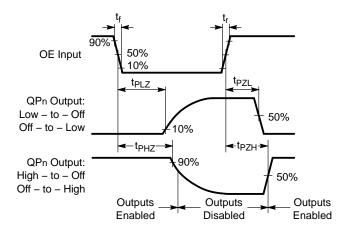
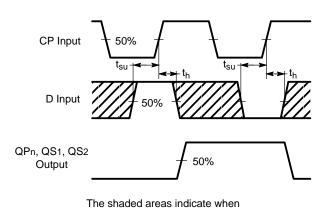


Figure 7. Waveforms showing the clock (CP) to output (QPn, QS1, QS2) propagation delays, the clock pulse width and the maximum clock frequency.

Figure 8. Waveforms showing the strobe (STR) to output (QPn) propagation delays, the strobe pulse width, the clock set-up and hold times for the strobe input.



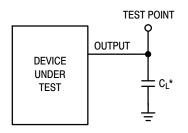


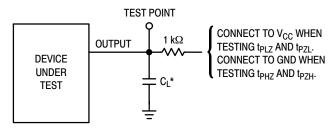
the input is permitted to change for predictable output performance.

Figure 9. Waveforms showing the 3-state enable and disable times for input OE.

Figure 10. Waveforms showing the data set-up and hold times for the data input.

TEST CIRCUITS





*Includes all probe and jig capacitance

Figure 11. AC Characteristics Load Circuits

ORDERING INFORMATION

Device	Package	Shipping [†]
MC74HC4094ADG	SOIC-16 (Pb-Free)	48 Units / Rail
MC74HC4094ADR2G	SOIC-16 (Pb-Free)	2500 / Tape & Reel
MC74HC4094ADTG	TSSOP-16 (Pb-Free)	96 Units / Rail
MC74HC4094ADTR2G	TSSOP-16 (Pb-Free)	2500 / Tape & Reel
NLVHC4094BDTR2G*	TSSOP-16 (Pb-Free)	2500 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{*}Includes all probe and jig capacitance

^{*}NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.



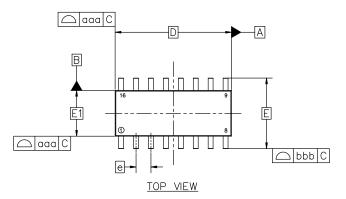


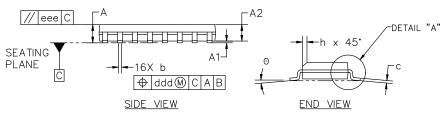
SOIC-16 9.90x3.90x1.50 1.27P CASE 751B ISSUE L

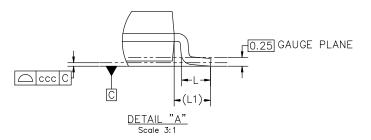
DATE 29 MAY 2024

NOTES:

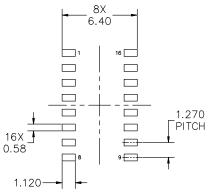
- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
- 2. DIMENSION IN MILLIMETERS. ANGLE IN DEGREES.
- 3. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD PROTRUSION.
- 4. MAXIMUM MOLD PROTRUSION 0.15mm PER SIDE.
- DIMENSION 6 DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127mm TOTAL IN EXCESS OF THE 6 DIMENSION AT MAXIMUM MATERIAL CONDITION.







MILLIMETERS							
DIM	MIN NOM MAX						
А	1.35	1.55	1.75				
A1	0.00	0.05	0.10				
A2	1.35	1.50	1.65				
b	0.35	0.42	0.49				
С	0.19	0.22	0.25				
D		9.90 BSC					
E		6.00 BSC					
E1		3.90 BSC					
е		1.27 BSC					
h	0.25		0.50				
L	0.40	0.83	1.25				
L1		1.05 REF					
Θ	0.		7*				
TOLERAN	CE OF FORM AND POSITION						
aaa	0.10						
bbb	0.20						
ccc	0.10						
ddd		0.25					
eee		0.10					



RECOMMENDED MOUNTING FOOTPRINT

*FOR ADDITIONAL INFORMATION ON OUR
PB-FREE STRATEGY AND SOLDERING DETAILS,
PLEASE DOWNLOAD THE onsemi SOLDERING
AND MOUNTING TECHNIQUES REFERENCE
MANUAL, SOLDERRM/D

DOCUMENT NUMBER:	98ASB42566B	Electronic versions are uncontrolled except when accessed directly from the Document F Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	SOIC-16 9.90X3.90X1.50 1	.27P	PAGE 1 OF 2

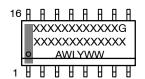
onsemi and ONSemi are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.



SOIC-16 9.90x3.90x1.50 1.27P CASE 751B ISSUE L

DATE 29 MAY 2024

GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code

A = Assembly Location

WL = Wafer Lot
 Y = Year
 WW = Work Week
 G = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

077/15/		077/15.0		071/15 0		T	
STYLE 1: PIN 1.	COLLECTOR	STYLE 2:	CATHODE	STYLE 3: PIN 1.		TYLE 4: PIN 1.	COLLECTOR DVF #1
PIN 1. 2.		PIN 1. 2.		PIN 1. 2.	COLLECTOR, DYE #1 BASE, #1	2.	
2. 3.	EMITTER	2. 3.	NO CONNECTION				
				3.		3.	
4.	NO CONNECTION	4.		4.		4.	
5.	EMITTER	5.		5.		5.	
6.	BASE	6.		6.		6.	
7.		7.			EMITTER, #2		COLLECTOR, #4
8.		8.		8.			COLLECTOR, #4
9.		9.			COLLECTOR, #3		BASE, #4
10.			ANODE		BASE, #3		EMITTER, #4
	NO CONNECTION	11.			EMITTER, #3		BASE, #3
	EMITTER		CATHODE		COLLECTOR, #3		EMITTER, #3
	BASE		CATHODE		COLLECTOR, #4		BASE, #2
	COLLECTOR	14.			BASE, #4		EMITTER, #2
15.			ANODE		EMITTER, #4		BASE, #1
16.	COLLECTOR	16.	CATHODE	16.	COLLECTOR, #4	16.	EMITTER, #1
STYLE 5:		STYLE 6:		STYLE 7:			
STYLE 5: PIN 1.	DRAIN, DYE #1	STYLE 6: PIN 1.	CATHODE	STYLE 7: PIN 1.	SOURCE N-CH		
	DRAIN, DYE #1 DRAIN, #1			PIN 1.	SOURCE N-CH COMMON DRAIN (OUTPUT)		
PIN 1.	,	PIN 1.	CATHODE	PIN 1.	COMMON DRAIN (OUTPUT)		
PIN 1. 2.	DRAIN, #1	PIN 1. 2.	CATHODE CATHODE	PIN 1. 2.	COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT)		
PIN 1. 2. 3.	DRAIN, #1 DRAIN, #2	PIN 1. 2. 3.	CATHODE CATHODE	PIN 1. 2. 3.	COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT)		
PIN 1. 2. 3. 4.	DRAIN, #1 DRAIN, #2 DRAIN, #2	PIN 1. 2. 3. 4.	CATHODE CATHODE CATHODE CATHODE	PIN 1. 2. 3. 4.	COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) GATE P-CH COMMON DRAIN (OUTPUT)		
PIN 1. 2. 3. 4. 5.	DRAIN, #1 DRAIN, #2 DRAIN, #2 DRAIN, #3	PIN 1. 2. 3. 4. 5.	CATHODE CATHODE CATHODE CATHODE	PIN 1. 2. 3. 4. 5.	COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) GATE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT)		
PIN 1. 2. 3. 4. 5.	DRAIN, #1 DRAIN, #2 DRAIN, #2 DRAIN, #3 DRAIN, #3 DRAIN, #4	PIN 1. 2. 3. 4. 5.	CATHODE CATHODE CATHODE CATHODE CATHODE	PIN 1. 2. 3. 4. 5.	COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) GATE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT)		
PIN 1. 2. 3. 4. 5. 6. 7.	DRAIN, #1 DRAIN, #2 DRAIN, #2 DRAIN, #3 DRAIN, #3	PIN 1. 2. 3. 4. 5. 6.	CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE	PIN 1. 2. 3. 4. 5. 6.	COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) GATE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) SOURCE P-CH		
PIN 1. 2. 3. 4. 5. 6. 7.	DRAIN, #1 DRAIN, #2 DRAIN, #2 DRAIN, #3 DRAIN, #3 DRAIN, #4 DRAIN, #4	PIN 1. 2. 3. 4. 5. 6. 7.	CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE ANODE	PIN 1. 2. 3. 4. 5. 6. 7.	COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) GATE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) SOURCE P-CH SOURCE P-CH		
PIN 1. 2. 3. 4. 5. 6. 7. 8. 9.	DRAIN, #1 DRAIN, #2 DRAIN, #2 DRAIN, #3 DRAIN, #3 DRAIN, #4 DRAIN, #4 SOURCE, #4	PIN 1. 2. 3. 4. 5. 6. 7. 8. 9.	CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE ANODE ANODE	PIN 1. 2. 3. 4. 5. 6. 7. 8. 9.	COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) GATE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) SOURCE P-CH SOURCE P-CH COMMON DRAIN (OUTPUT)		
PIN 1. 2. 3. 4. 5. 6. 7. 8. 9.	DRAIN, #1 DRAIN, #2 DRAIN, #2 DRAIN, #3 DRAIN, #3 DRAIN, #4 DRAIN, #4 GATE, #4 SOURCE, #4 GATE, #3	PIN 1. 2. 3. 4. 5. 6. 7. 8. 9.	CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE ANODE ANODE	PIN 1. 2. 3. 4. 5. 6. 7. 8.	COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) GATE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) SOURCE P-CH SOURCE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT)		
PIN 1. 2. 3. 4. 5. 6. 7. 8. 9.	DRAIN, #1 DRAIN, #2 DRAIN, #2 DRAIN, #3 DRAIN, #3 DRAIN, #4 DRAIN, #4 SOURCE, #4	PIN 1. 2. 3. 4. 5. 6. 7. 8. 9.	CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE ANODE ANODE ANODE ANODE ANODE ANODE ANODE	PIN 1. 2. 3. 4. 5. 6. 7. 8. 9.	COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) GATE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) SOURCE P-CH SOURCE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT)		
PIN 1. 2. 3. 4. 5. 6. 7. 8. 9. 10.	DRAIN, #1 DRAIN, #2 DRAIN, #2 DRAIN, #3 DRAIN, #3 DRAIN, #4 GATE, #4 SOURCE, #4 GATE, #3 SOURCE, #3 GATE, #2	PIN 1. 2. 3. 4. 5. 6. 7. 8. 9. 10. 11. 12.	CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE ANODE ANODE ANODE ANODE ANODE ANODE ANODE	PIN 1. 2. 3. 4. 5. 6. 7. 8. 9. 10.	COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) GATE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) SOURCE P-CH SOURCE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) GOMMON DRAIN (OUTPUT) GATE N-CH		
PIN 1. 2. 3. 4. 5. 6. 7. 8. 9. 10. 11. 12.	DRAIN, #1 DRAIN, #2 DRAIN, #2 DRAIN, #3 DRAIN, #3 DRAIN, #4 DRAIN, #4 DRAIN, #4 GATE, #4 SOURCE, #4 GATE, #3 SOURCE, #3 GATE, #2 SOURCE, #2 SOURCE, #2	PIN 1. 2. 3. 4. 5. 6. 7. 8. 9. 10. 11. 12.	CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE ANODE	PIN 1. 2. 3. 4. 5. 6. 7. 8. 9. 10. 11. 12. 13.	COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) GATE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) SOURCE P-CH SOURCE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) CATE N-CH COMMON DRAIN (OUTPUT)		
PIN 1. 2. 3. 4. 5. 6. 7. 8. 9. 10. 11. 12.	DRAIN, #1 DRAIN, #2 DRAIN, #2 DRAIN, #3 DRAIN, #3 DRAIN, #4 GATE, #4 SOURCE, #4 GATE, #3 SOURCE, #3 GATE, #2	PIN 1. 2. 3. 4. 5. 6. 7. 8. 9. 10. 11. 12. 13.	CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE ANODE	PIN 1. 2. 3. 4. 5. 6. 7. 8. 9. 10. 11. 12.	COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) GATE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) SOURCE P-CH SOURCE P-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) GATE N-CH COMMON DRAIN (OUTPUT)		

DOCUMENT NUMBER:	98ASB42566B	Electronic versions are uncontrolled except when accessed directly from the Document Rep Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	SOIC-16 9.90X3.90X1.50 1	.27P	PAGE 2 OF 2

onsemi and ONSEMI are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

2X L/2

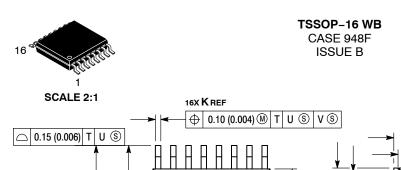
L

☐ 0.15 (0.006)

PIN 1 IDENT.

υ®





DATE 19 OCT 2006

NOTES

Κ

SECTION N-N

0.25 (0.010)

J1

В

-U-

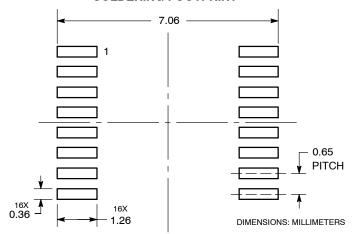
- DIMENSIONING AND TOLERANCING PER
- ANSI Y14.5M, 1982. CONTROLLING DIMENSION: MILLIMETER.
- DIMENSION A DOES NOT INCLUDE MOLD FLASH. PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT
- EXCEED 0.15 (0.006) PER SIDE.
 DIMENSION B DOES NOT INCLUDE
 INTERLEAD FLASH OR PROTRUSION.
- INTERLEAD FLASH OR PROTRUSION.
 INTERLEAD FLASH OR PROTRUSION SHALL
 NOT EXCEED 0.25 (0.010) PER SIDE.
 DIMENSION K DOES NOT INCLUDE DAMBAR
 PROTRUSION. ALLOWABILE DAMBAR
 PROTRUSION SHALL BE 0.08 (0.003) TOTAL
 IN EXCESS OF THE K DIMENSION AT
 MAXIMUM MATERIAL CONDITION.
 TERMINIAL NILMBERS ADE SUCIUMI ECIP.
- TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
- DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIMETERS					HES
DIM	MIN	MAX	MIN	MAX		
Α	4.90	5.10	0.193	0.200		
В	4.30	4.50	0.169	0.177		
С		1.20		0.047		
D	0.05	0.15	0.002	0.006		
F	0.50	0.75	0.020	0.030		
G	0.65	BSC	0.026 BSC			
Н	0.18	0.28	0.007	0.011		
7	0.09	0.20	0.004	0.008		
J1	0.09	0.16	0.004	0.006		
K	0.19	0.30	0.007	0.012		
K1	0.19	0.25	0.007	0.010		
L	6.40	BSC	0.252 BSC			
М	00	00	00	0 0		

DETAIL E -W-☐ 0.10 (0.004) **DETAIL E** SEATING PLANE D

RECOMMENDED SOLDERING FOOTPRINT*

-V-



^{*}For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



= Specific Device Code XXXX Α = Assembly Location

= Wafer Lot L = Year W = Work Week G or • = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present. Some products may not follow the Generic Marking.

DOCUMENT NUMBER:	98ASH70247A	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	TSSOP-16		PAGE 1 OF 1

onsemi and ONSEMI are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

onsemi, Onsemi, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. Onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA class 3 medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:

 $\textbf{Technical Library:} \ \underline{www.onsemi.com/design/resources/technical-documentation}$

onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at

www.onsemi.com/support/sales